

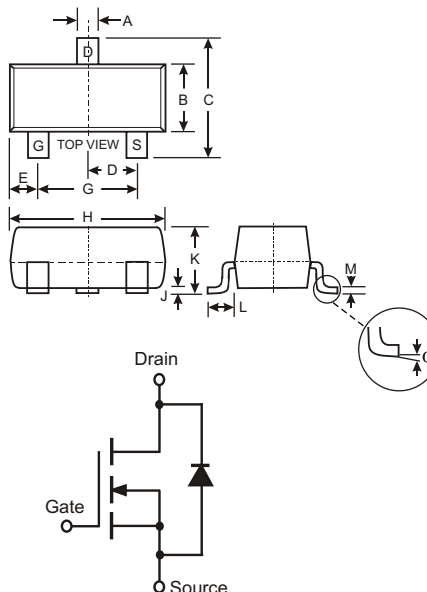
## N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

### Mechanical Data

- Case: SOT-23, Molded Plastic
- Case Material - UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking (See Page 2): K70
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approx.)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
$\alpha$	0°	8°
All Dimensions in mm		

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	BS870	Units
Drain-Source Voltage	$V_{DS}$	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0\text{M}\Omega$	$V_{DGR}$	60	V
Gate-Source Voltage Continuous	$V_{GSS}$	$\pm 20$	V
Drain Current (Note 1) Continuous	$I_D$	250	mA
Total Power Dissipation (Note 1)	$P_d$	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	K/W
Operating and Storage Temperature Range	$T_j, T_{STG}$	-55 to +150	$^\circ\text{C}$

Note: 1. Device mounted on FR-5 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

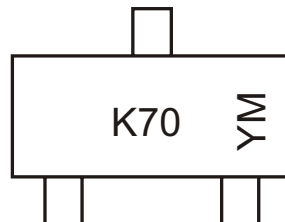
**Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	80	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 100μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	0.5	μA	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±10	nA	V <sub>GS</sub> = ±15V, V <sub>DS</sub> = 0V
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	2.0	3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	—	3.5	5.0	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.2A
On-State Drain Current	I <sub>D(ON)</sub>	—	1.0	0.5	A	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance	g <sub>FS</sub>	80	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C <sub>iss</sub>	—	22	50	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	11	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	2.0	5.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t <sub>D(ON)</sub>	—	2.0	20	ns	V <sub>ES</sub> = 10V, R <sub>L</sub> = 150Ω, V <sub>DS</sub> = 10V, R <sub>D</sub> = 100Ω
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	5.0	20	ns	

**Ordering Information** (Note 3)

Device	Packaging	Shipping
BS870-7	SOT-23	3000/Tape & Reel

Notes: 2. Short duration test pulse used to minimize self-heating effect.  
 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**


K70 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: N = 2002  
 M = Month ex: 9 = September

**Date Code Key**

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

